CRJD600N80G2E

SJMOS N-MOSFET 800V, 490mΩ, 9A

Features

- CRM(CQ) Super_Junction technology
- Much lower Ron*A performance for On-state efficiency
- Better efficiency due to very low FOM
- Integrated ESD protection diode
- Qualified for industrial grade applications according to JEDEC

Product Summary

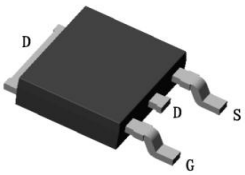
$V_{DS,min}$	800V
$R_{DS(on),typ}$	490mΩ
I_D	9A
ESD(HBM)	2000V

Applications

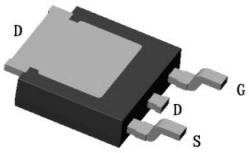
- LED/LCD/PDP TV and monitor Lighting
- Solar/Renewable/UPS-Micro Inverter System
- Charger
- Power Supply

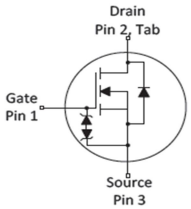
100% DVDS Tested
100% Avalanche Tested

Top view



Bottom view





Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRJD600N80G2E	J600N80G2E	TO-252	Tape&Reel	N/A	N/A	2500pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
Continuous drain current [1)] T_C = 25°C T_C = 100°C	I_D	 9 5	A
Pulsed drain current [2)] (T_C = 25°C, t_p limited by $T_{j,max}$)	$I_{D,pulse}$	34	A
Avalanche energy, single pulse (L=30mH)	E_{AS}	86	mJ
MOSFET dv/dt ruggedness	dv/dt	50	V/ns
Gate-Source voltage	V_{GS}	±30	V
Power dissipation (T_C = 25°C)	P_{tot}	105	W
Continuous diode forward current(T_C = 25°C)	I_S	9	A
Diode pulse current [2)] (T_C = 25°C)	$I_{S,pulse}$	34	A
Recovery diode dv/dt [3)]	dv/dt	50	V/ns
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

1) Limited by $T_{j,max}$. Maximum Duty Cycle D = 0.50
2) Pulse width t_p limited by $T_{j,max}$
3) Identical low side and high side switch with identical R_g

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case	R_{thJC}	-	0.85	1.19	°C/W	
Thermal resistance, junction – ambient	R_{thJA}	-	-	121	°C/W	

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	800	-	-	V	V_{GS}=0V,I_D=250μA
Gate threshold voltage	$V_{GS(th)}$	3	-	4	V	V_{DS}=V_{GS},I_D=250μA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=800V,V_{GS}=0V T_j=25°C
		-	5	-		T_j=150°C
Gate-source leakage current	I_{GSS}	-	-	±10	μA	V_{GS}=±30V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	490	600	mΩ	V_{GS}=10V,I_D=4A, T_j=25°C
		-	1150	-		T_j=150°C
Transconductance	g_{fs}	-	4.7	-	S	V_{DS}=20V,I_D=4A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	600	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output Capacitance	C_{oss}	-	24.4	-		
Reverse Transfer Capacitance	C_{rss}	-	1.65	-		
Gate Total Charge	Q_g	-	18.3	-	nC	V_{GS}=10V, V_{DS}=480V, I_D=4A
Gate-Source charge	Q_{gs}	-	4.7	-		
Gate-Drain charge	Q_{gd}	-	8.1	-		
Gate plateau voltage	$V_{plateau}$	-	6	-	V	
Turn-on delay time	$t_{d(on)}$	-	19	-	ns	V_{GS}=10V, I_D=4A, V_{DS}=400V, R_g=27Ω
Rise time	t_r	-	37	-		
Turn-off delay time	$t_{d(off)}$	-	82	-		
Fall time	t_f	-	35	-		
Gate resistance	$R_{g,int}$	-	10.3	-	Ω	f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.83	1	V	V_{GS}=0V,I_{SD}=4A
Body Diode Reverse Recovery Time	t_{rr}	-	292	-	ns	I_{SD}=4A di_F/dt=100A/μs V_{DS}=400V
Body Diode Reverse Recovery Charge	Q_{rr}	-	2.9	-	μC	
Body Diode Reverse Recovery Peak Current	I_{rrm}	-	19.4	-	A	

Typical Performance Characteristics

Fig 1. Output Characteristics (T_j=25℃)

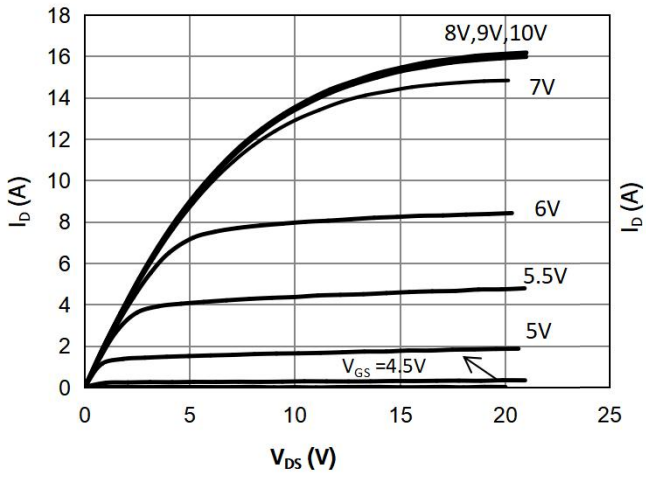


Fig 2. Output Characteristics (T_j=150℃)

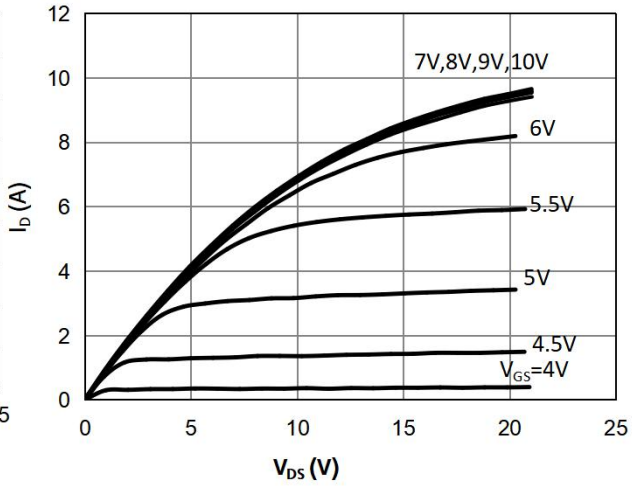


Fig 3: Transfer Characteristics

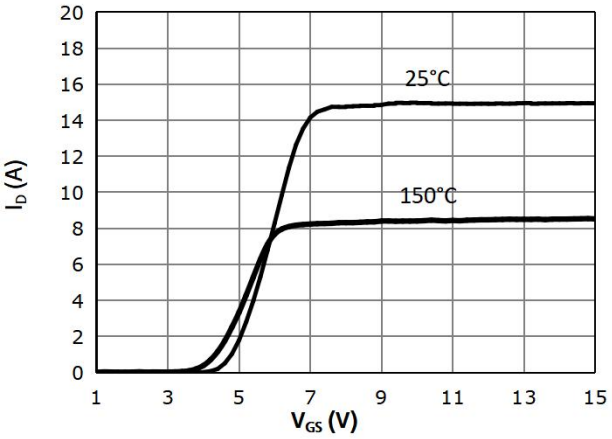


Fig 4: V_{TH} vs. T_j Temperature Characteristics

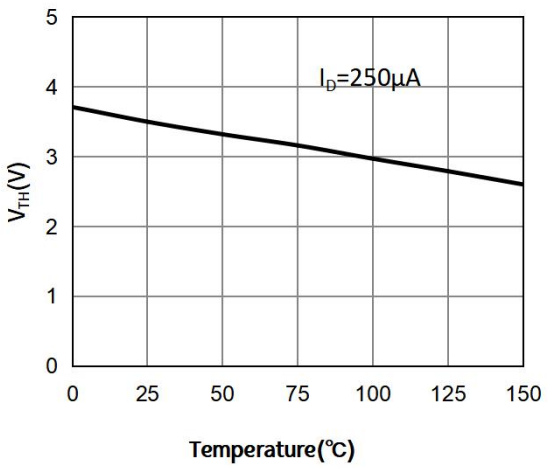


Fig 5: $R_{DS(on)}$ vs. I_{DS} Characteristics(T_j=25℃)

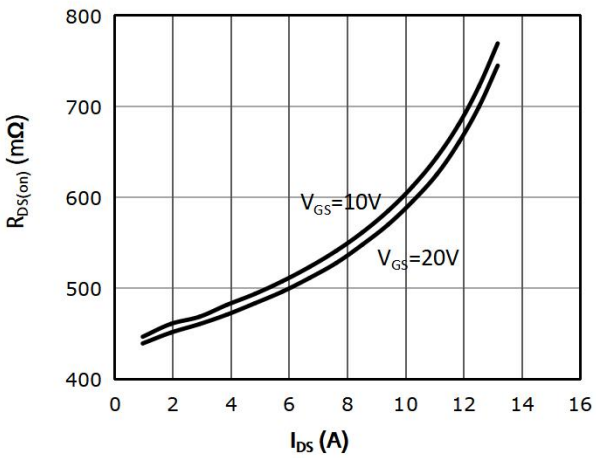


Fig 6: $R_{DS(on)}$ vs. Temperature

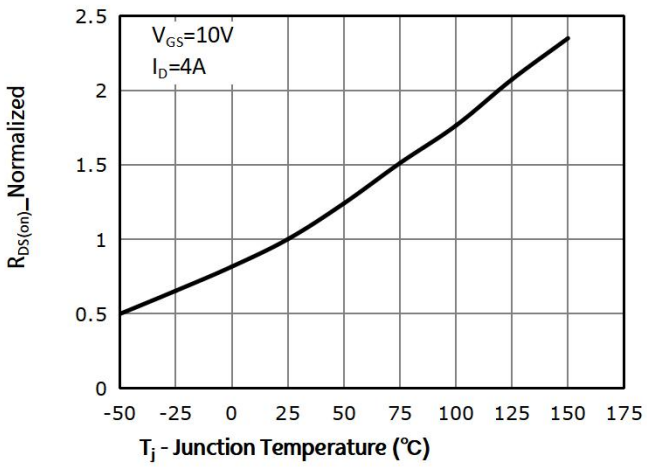


Fig 7: BV_{DSS} vs. Temperature

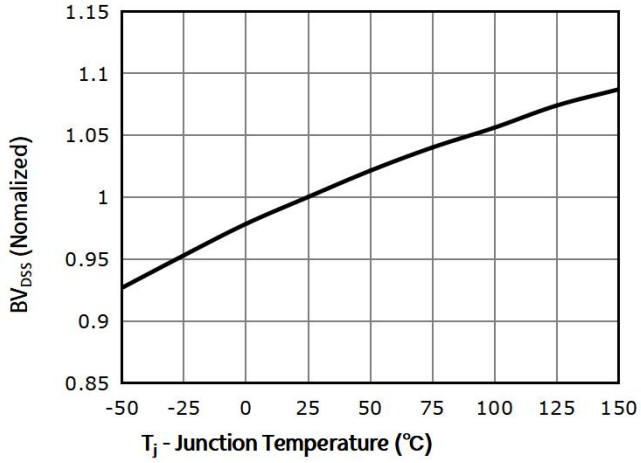


Fig 8: $R_{DS(on)}$ vs. Gate Voltage

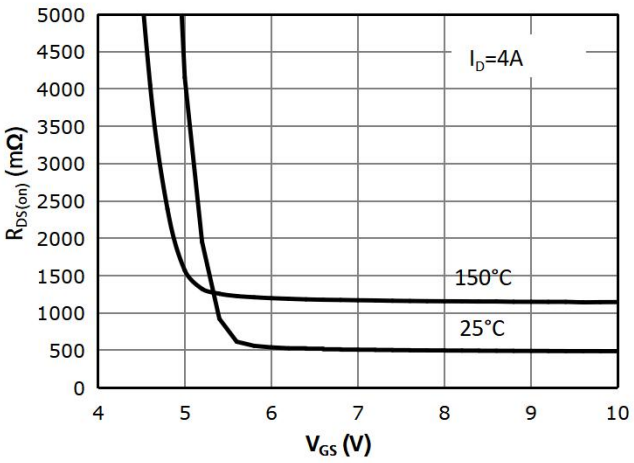


Fig 9: Body-diode Forward Characteristics

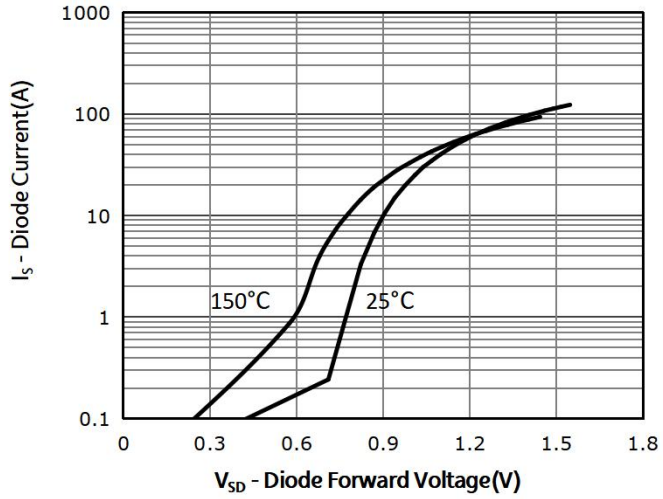


Fig 10: Gate Charge Characteristics

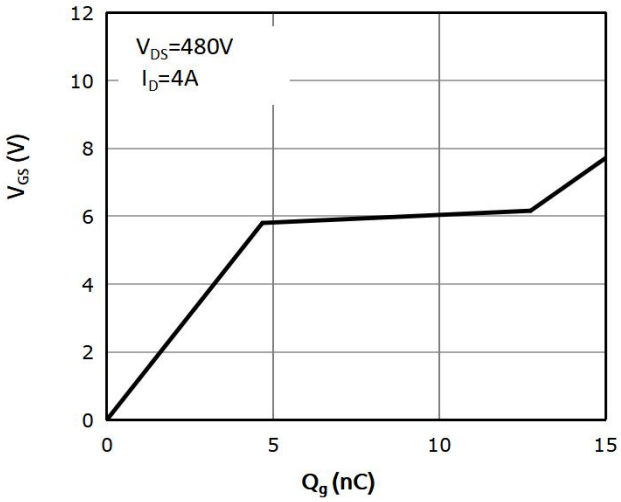


Fig 11: Capacitance Characteristics

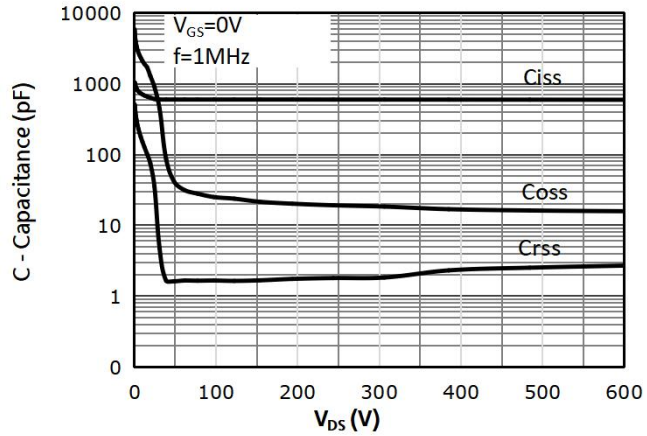


Fig 12: Safe Operating Area

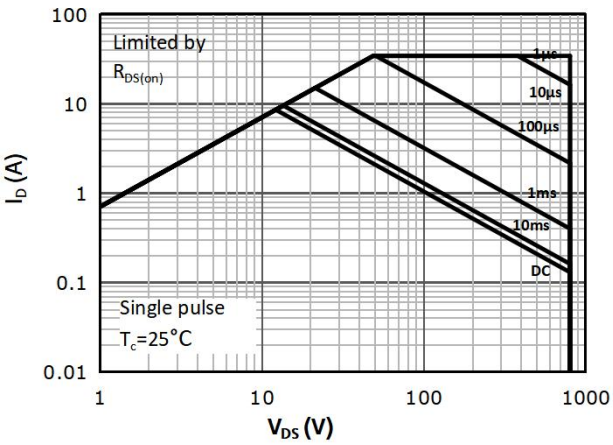
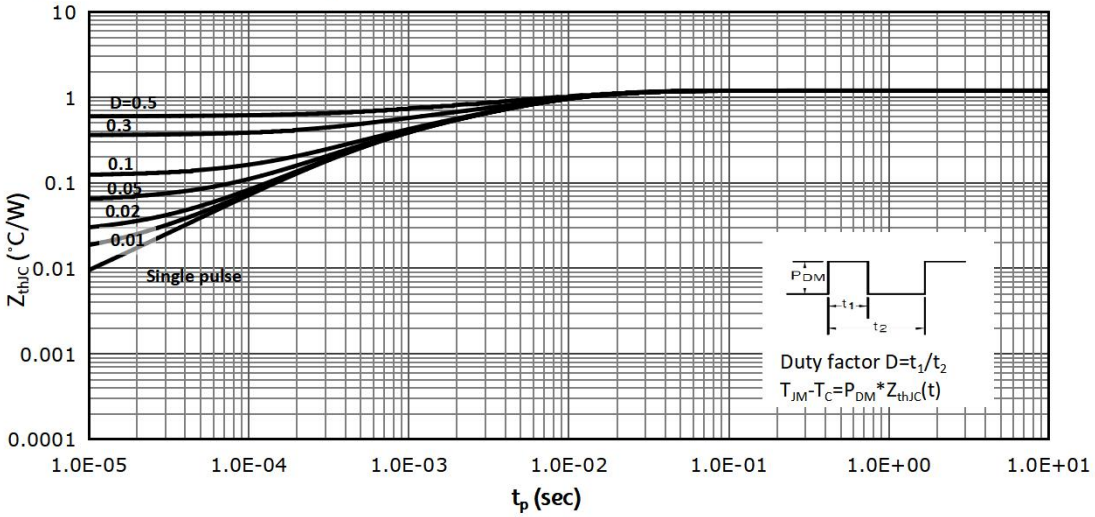
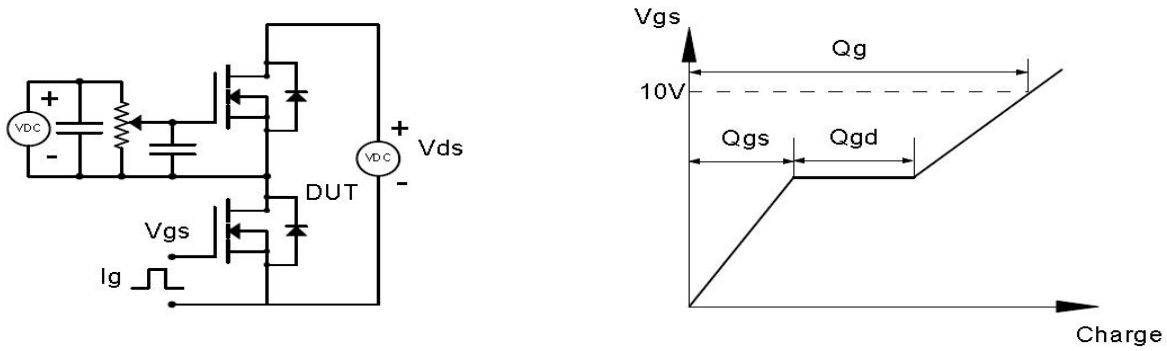


Fig 13: Max. Transient Thermal Impedance

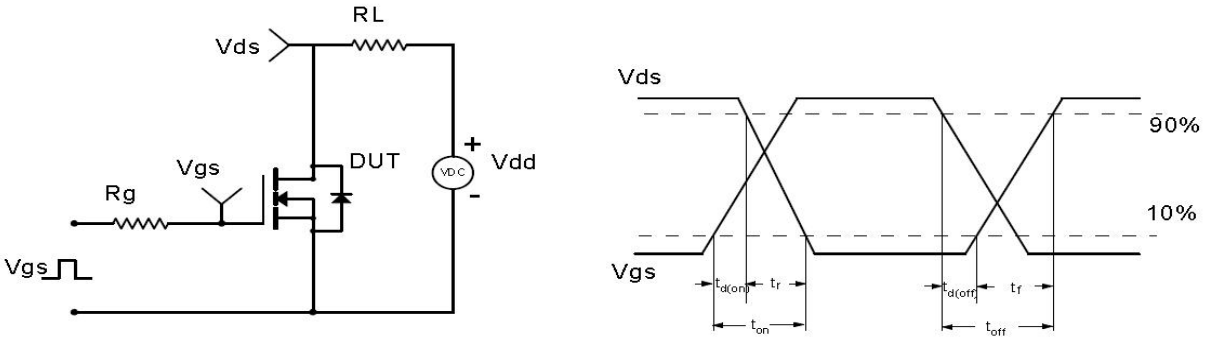


Test Circuit & Waveform

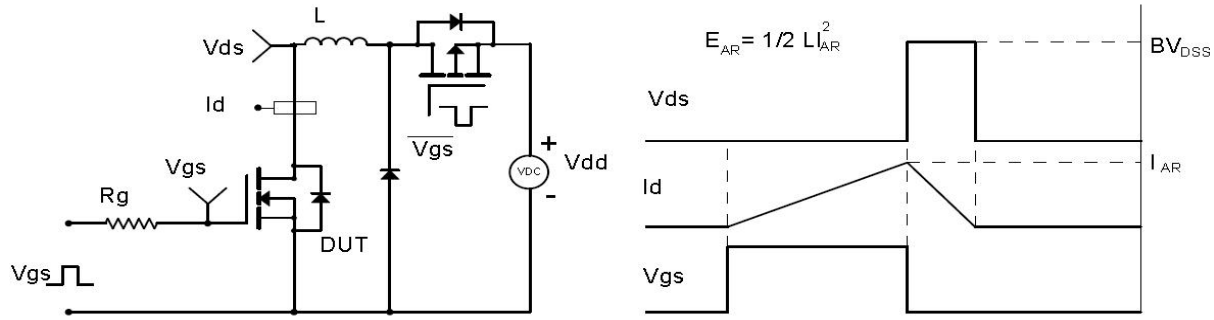
Gate Charge Test Circuit & Waveform



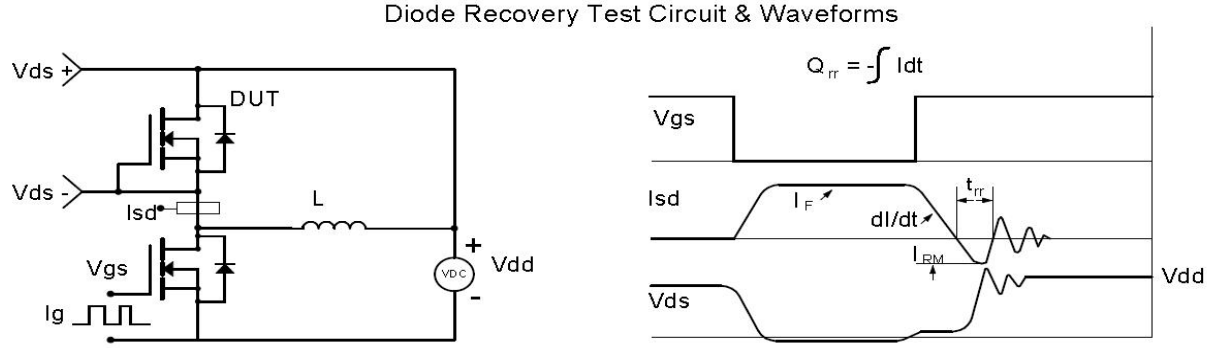
Resistive Switching Test Circuit & Waveforms



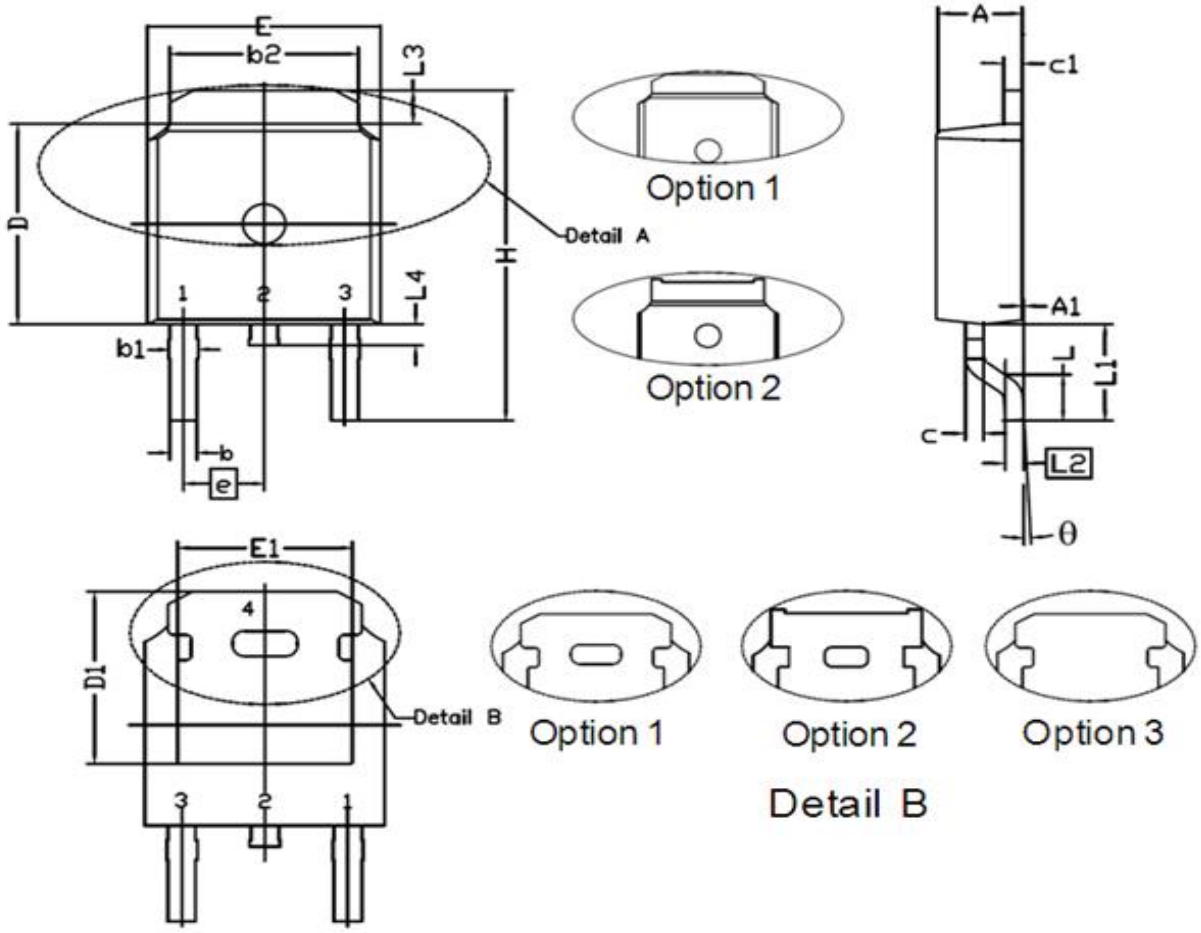
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
A1	0.00	0.15	0.000	0.006
b	0.60	0.91	0.024	0.036
b1	0.65	1.15	0.026	0.045
b2	5.00	5.64	0.197	0.222
c	0.45	0.61	0.018	0.024
c1	0.36	0.66	0.014	0.026
D	5.80	6.30	0.228	0.248
D1	5.21	--	0.205	--
e	2.29 BSC.		0.090 BSC.	
E	6.30	6.90	0.248	0.272
E1	4.40	--	0.173	--
H	9.40	10.48	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.92 REF		0.115 REF	
L2	0.508 BSC.		0.020 BSC.	
L3	0.72	1.35	0.028	0.053
L4	0.60	1.20	0.024	0.047
θ	0°	10°	0°	10°

Marking



NOTE:
NXBBAAAA

N	—WB code (Usually omitted)
X	—Assembly location code
BB	—Fab code
AAAA	—Lot code

Revision History

Revison	Major changes
1.1	Update to new template
2.0	Formal version
2.1	Adjust data format

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.